

2N3789
 thru
 2N3792

SILICON PNP POWER TRANSISTORS

MAXIMUM RATINGS

Characteristic	Symbol	2N3789 2N3791	2N3790 2N3792	Unit
Collector-Base Voltage	V_{CB}	60	80	Volts
Collector-Emitter Voltage	V_{CEO}	60	80	Volts
Emitter-Base Voltage	V_{EB}	7.0	7.0	Volts
Collector Current (Continuous)	I_C	10	10	Amps
Base Current (Continuous)	I_B	4.0	4.0	Amps
Power Dissipation	P_D	150	150	Watts
Thermal Resistance	θ_{JC}	1.17	1.17	$^{\circ}C/W$
Junction Operating and Storage Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}C$

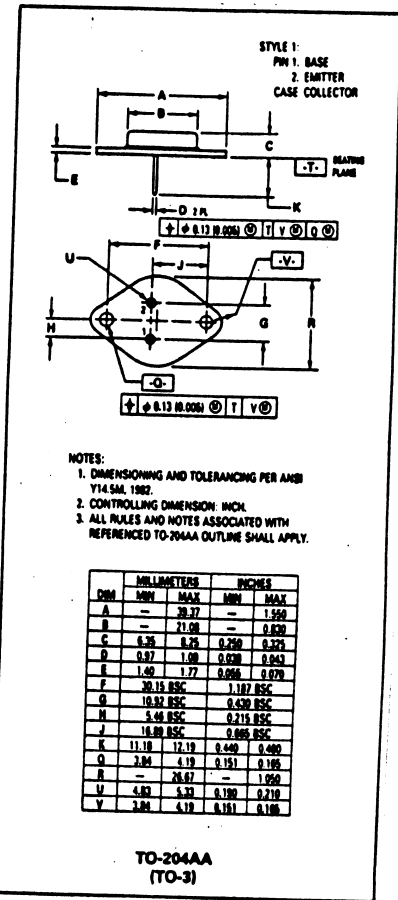
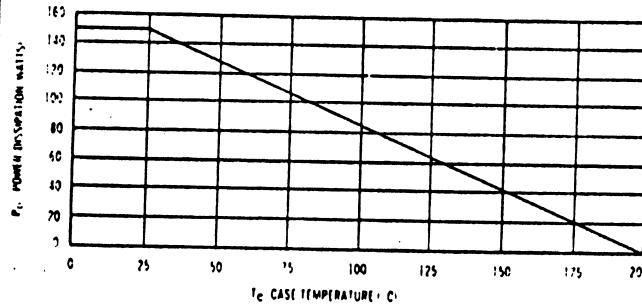
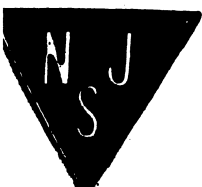


FIGURE 1 - POWER-TEMPERATURE DERATING CURVE



Safe Area Limits are indicated by Figures 15, 16. Both limits are applicable and must be observed.



ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
Collector-Emitter Sustaining Voltage* ($I_C = 200\text{ mA}$, $I_B = 0$)	2N3789, 2N3791 2N3790, 2N3792	$V_{CE(sus)}$ *	60 80	- -	Vdc
Collector-Emitter Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $V_{BE} = -1.5\text{ Vdc}$) ($V_{CE} = 80\text{ Vdc}$, $V_{BE} = -1.5\text{ Vdc}$) ($V_{CE} = 60\text{ Vdc}$, $V_{BE} = -1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$) ($V_{CE} = 80\text{ Vdc}$, $V_{BE} = -1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$)	2N3789, 2N3791 2N3790, 2N3792 2N3789, 2N3791 2N3790, 2N3792	I_{CEX}	- - - -	1 1 5 5	mA
Emitter-Base Cutoff Current ($V_{EB} = 7\text{ Vdc}$)	All Types	I_{EBO}	-	5	mA
DC Current Gain* ($I_C = 1\text{ A}$, $V_{CE} = 2\text{ Vdc}$) ($I_C = 3\text{ A}$, $V_{CE} = 2\text{ Vdc}$)	2N3789, 2N3790 2N3791, 2N3792 2N3789, 2N3790 2N3791, 2N3792	h_{FE} *	25 50 15 30	90 180 - -	-
Collector-Emitter Saturation Voltage* ($I_C = 4\text{ A}$, $I_B = 0.4\text{ A}$) ($I_C = 5\text{ A}$, $I_B = 0.5\text{ A}$)	2N3789, 2N3790 2N3791, 2N3792	$V_{CE(sat)}$ *	- -	1.0 1.0	Vdc
Base-Emitter On Voltage* ($I_C = 5\text{ A}$, $V_{CE} = 2\text{ Vdc}$) ($I_C = 10\text{ A}$, $V_{CE} = 4\text{ Vdc}$)	2N3789, 2N3790 2N3791, 2N3792 All Types	$V_{BE(on)}$ *	- - -	2.0 1.8 4.0	Vdc
Current Gain - Bandwidth Product ($V_{CE} = 10\text{ Vdc}$, $I_C = 0.5\text{ A}$, $f = 1\text{ MHz}$)	All Types	f_T	4	-	MHz

*Sweep Test: 1/2 sine wave cycle @ 60 cps